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APPLICATION NO.	FI	LING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/611,896 07/03/2003		07/03/2003	Yu-Chou Lee	MR3029-77	3708
4586	7590	03/01/2006		EXAM	INER
ROSENBE	RG, KLE	EIN & LEE	TRAN, THIEN F		
3458 ELLIC	OTT CEN	ITER DRIVE-SUITE	E 101		
ELLICOTT CITY, MD 21043				ART UNIT	PAPER NUMBER
				2011	· · · · · · · · · · · · · · · · · · ·

DATE MAILED: 03/01/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/611,896	LEE ET AL.				
Office Action Summary	Examiner	Art Unit				
	Thien F. Tran	2811				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on 22 L	<u> </u>					
<u></u>	, _					
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
closed in accordance with the practice under a	⊏x parte Quayle, 1935 G.D. 11, 40	53 U.G. 213.				
Disposition of Claims						
4) ☐ Claim(s) 1-15 is/are pending in the application 4a) Of the above claim(s) is/are withdra 5) ☐ Claim(s) 9-15 is/are allowed. 6) ☐ Claim(s) 1-5 is/are rejected. 7) ☐ Claim(s) 6-8 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o Application Papers 9) ☐ The specification is objected to by the Examine 10) ☐ The drawing(s) filed on is/are: a) ☐ according to the application and formula is/a	or election requirement.	Examiner.				
Applicant may not request that any objection to the	drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).				
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
 12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documen 2. Certified copies of the priority documen 3. Copies of the certified copies of the priority application from the International Burea * See the attached detailed Office action for a list 	ts have been received. ts have been received in Applicati prity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage				
Attachment(s)						
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:					

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 1, 3 and 5 are rejected under 35 U.S.C. 102(b) as being anticipated by Wakagi et al. (US 5,995,187).

Wakagi et al. disclose a thin-film transistor structure (Fig. 5) comprising: an insulating substrate (1); a gate electrode (2) on said insulating substrate; a dielectric layer (4) over said gate electrode; a first semiconductive layer (5) on said dielectric layer; a second semiconductive layer (6) on said first semiconductive layer (5); a conductive electrode (7, 8) of CrMo alloy film on said second semiconductive layer as a source and a drain electrode; wherein said second semiconductive layer (6) and said conductive electrode (7, 8) have an opening therethrough and exposing said first semiconductive layer (5). Claimed structure does not require a first conductive layer, a second conductive layer and a third conductive layer formed of different materials. Therefore, three portions of the conductive electrode (7, 8) could be characterized as three conductive layers; wherein the bottom portion of the source or drain electrode (7,8) corresponds to a first conductive layer, the middle portion of source or drain electrode (7,8) corresponds to a second conductive layer and the top portion of the source or drain electrode (7,8) corresponds to a third conductive layer, wherein the first,

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the second and the third conductive layers are made of alloy layers each having two same main metal components (Cr and Mo).

Regarding claim 3, the dielectric layer (4) comprises a silicon nitride layer.

Regarding claim 5, the second semiconductive layer (6) comprises an N-type amorphous silicon layer.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 2 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wakagi et al. (US 5,995,187) in view of Harano et al. (US 6,317,185).

Wakagi et al. as described above do not disclose the gate electrode (2) comprising an AINd gate electrode. Harano et al. disclose a gate electrode (1) comprising an AINd gate electrode. It would have been obvious to a person having ordinary skill in the art at the time the invention was made to form the gate electrode (2) comprising an AINd gate electrode as taught by Harano in order to reduce hillocks and resistivity in the gate electrode.

Claim 4 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wakagi et al. (US 5,995,187) in view of Hayama (US 5,416,341).

Wakagi et al. as described above disclose the first semiconductor layer (5) comprising an amorphous silicon layer. Wakagi et al. do not expressly disclose the

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amorphous silicon layer (5) being a hydrogenated amorphous silicon layer. Hayama discloses thin film transistors comprising a hydrogenated amorphous silicon active layer. It would have been obvious to a person having ordinary skill in the art at the time the invention was made to form the amorphous silicon layer (5) of a hydrogenated amorphous silicon layer as taught by Hayama in order to have low leakage current between the source and drain regions.

Allowable Subject Matter

Claims 9-15 are allowed.

Claims 6-8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Response to Arguments

Applicant's arguments with respect to claims 1-5 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not

mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien F. Tran whose telephone number is (571) 272-1665. The examiner can normally be reached on 8:30AM - 5:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C. Lee can be reached on (571) 272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

tt February 24, 2006

